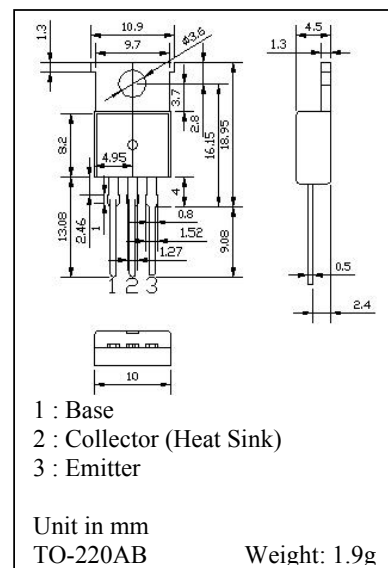


## TRIPLE DIFFUSED SILICON NPN TRANSISTOR

... designed for low frequency power amplifier

### MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	100	V
Collector Emitter Voltage	$V_{CEO}$	80	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current (DC)	$I_C$	4	A
Collector Current (Peak)	$I_C$	8	A
Collector power Dissipation	$P_C$	40	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C



### ELECTRICAL CHARACTERISTICS

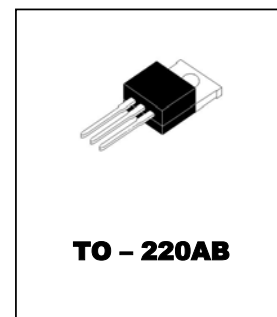
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut Off Current	$I_{CBO}$	$V_{CB} = 80V, I_E = 0A$	-	-	100	$\mu A$
Collector – Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA, I_B = 0A$	80	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE} = 4V, I_C = 1A$	60	-	200	-
		$V_{CE} = 4V, I_C = 0.1A$	35	-	-	-
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 0.2A$	-	-	1	V
Base Emitter Voltage	$V_{BE}$	$V_{CE} = 4V, I_C = 1A$	-	-	1.5	V
Transition Frequency	$f_T$	$V_{CE} = 5V, I_C = 0.5A$	-	10	-	MHz
Collector Out put Capacitance	$C_{ob}$	$V_{CB} = 20V, I_E = 0A, f=1MHz$	-	40	-	Pf

**HIGH POWER DISSIPATION**

**MEDIUM SPEED POWER SWITCHING**

### Classification of $h_{FE}$

Rank	B	C
Range	60 to 120	100-200



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